

# **KSC1222**

## **Low Frequency Low Noise Amplifier**

- Collector-Base Voltage: V<sub>CBO</sub>=50V
  Low Noise Level: NL=40mV (MAX.)



# **NPN Epitaxial Silicon Transistor**

## **Absolute Maximum Ratings** $T_a$ =25°C unless otherwise noted

Symbol	Parameter	Ratings	Units
$V_{CBO}$	Collector-Base Voltage	50	V
$V_{CEO}$	Collector-Emitter Voltage	45	V
$V_{EBO}$	Emitter-Base Voltage	5	V
I <sub>C</sub>	Collector Current	50	mA
P <sub>C</sub>	Collector Dissipation	250	mW
T <sub>J</sub>	Junction Temperature	150	°C
T <sub>STG</sub>	Storage Temperature	-55 ~ 150	°C

## **Electrical Characteristics** $T_a$ =25°C unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Units
BV <sub>CBO</sub>	Collector-Base Breakdown Voltage	$I_{C}=100\mu A, I_{E}=0$	50			V
BV <sub>CEO</sub>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> =10mA, I <sub>B</sub> =0	45			V
BV <sub>EBO</sub>	Emitter-Base Breakdown Voltage	$I_E=10\mu A, I_C=0$	5			V
I <sub>CBO</sub>	Collector Cut-off Current	$V_{CB}$ =50V, $I_E$ =0			50	nA
I <sub>EBO</sub>	Emitter Cut-off Current	$V_{EB}$ =5V, $I_{C}$ =0			100	nA
h <sub>FE</sub>	DC Current Gain	$V_{CE}$ =3V, $I_{C}$ =0.5mA	120		1000	
V <sub>CE</sub> (sat)	Collector-Emitter Saturation Voltage	I <sub>C</sub> =20mA, I <sub>B</sub> =2mA		0.1	0.2	V
V <sub>BE</sub> (on)	Base-Emitter On Voltage	$V_{CE}$ =3V, $I_{C}$ =0.5mA		0.62	0.7	V
f <sub>T</sub>	Current Gain Bandwidth Product	$V_{CE}=3V$ , $I_{C}=1mA$	50	100		MHz
NL	Noise Level	$V_{CE}$ =12V, $I_{C}$ = 0.1mA $R_{S}$ =25K $\Omega$ $A_{V}$ =80dB, f=1KHz		27	4.0	mV

# **h**<sub>FE</sub> Classification

Classification	Y	G	L	V
h <sub>FE</sub>	120 ~ 240	200 ~ 400	350 ~ 700	600 ~ 1000

# **Typical Characteristics**

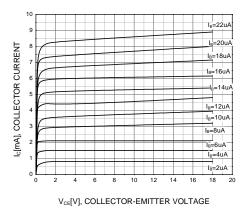


Figure 1. Static Characteristic

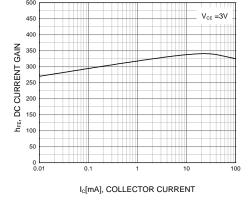


Figure 2. DC current Gain

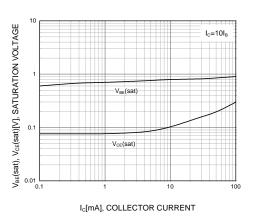


Figure 3. Base-Emitter Saturation Voltage Collector-Emitter Saturation Voltage

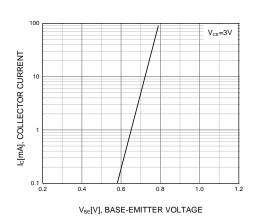


Figure 4. Base-Emitter On Voltage

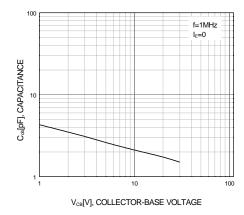


Figure 5. Output Capacitance

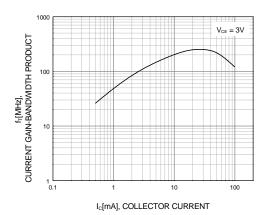


Figure 6. Current Gain Bandwidth Product

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# **Typical Characteristics** (Continued)

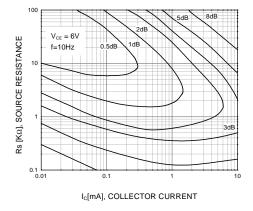


Figure 7. Noise Figure

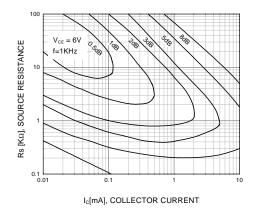


Figure 8. Noise Figure

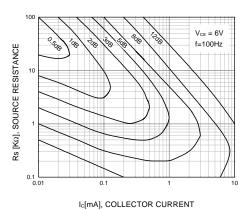


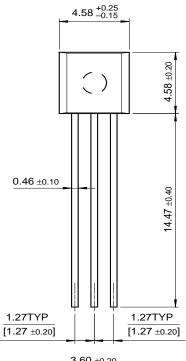
Figure 9. Noise Figure

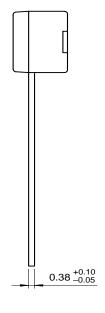
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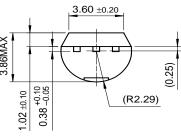


# KSC1222

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